

P-channel -30 V, 12 mΩ typ., -40 A STripFET™ H6 Power MOSFET in a DPAK package

Datasheet - production data

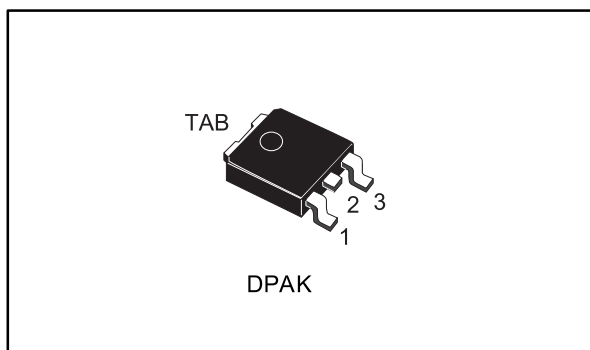
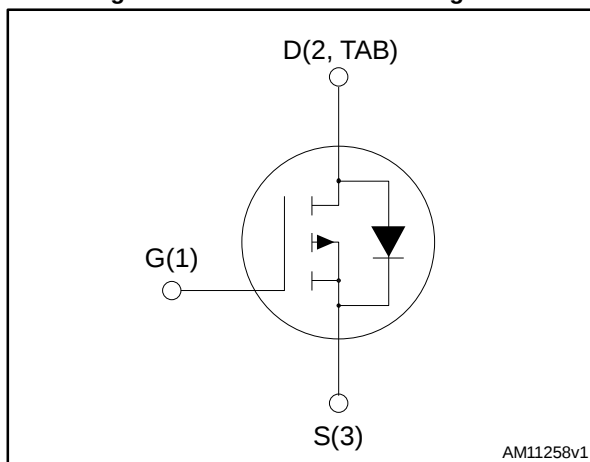


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STD40P3LLH6	-30 V	15 mΩ	-40 A

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is a P-channel Power MOSFET developed using the STripFET™ H6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.

Table 1: Device summary

Order code	Marking	Package	Packing
STD40P3LLH6	40P3LLH6	DPAK	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	-30	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	-40	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	-30.7	A
$I_{DM}^{(1)}$	Drain current (pulsed)	-160	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	60	W
T_{stg}	Storage temperature range	- 55 to 175	$^{\circ}\text{C}$
T_j	Operating junction temperature range		$^{\circ}\text{C}$

Notes:

⁽¹⁾Pulse width is limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.5	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50	

Notes:

⁽¹⁾When mounted on FR-4 board of 1 inch², 2oz Cu.

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified).

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0, I _D = -1 mA	-30			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0, V _{DS} = -30 V			-1	μA
		V _{GS} = 0, V _{DS} = -30 V, T _C = 125 °C ⁽¹⁾			-10	μA
I _{GSS}	Gate-body leakage current	V _{DS} = 0, V _{GS} = ± 20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = -250 μA	-1		-2.5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = -20 A		12	15	mΩ
		V _{GS} = -4.5 V, I _D = -20 A		18	22.5	mΩ

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = -25 V, f = 1 MHz, V _{GS} = 0	-	2615	-	pF
C _{oss}	Output capacitance		-	340	-	pF
C _{rss}	Reverse transfer capacitance		-	235	-	pF
Q _g	Total gate charge	V _{DD} = -15 V, I _D = -40 A, V _{GS} = -4.5 V (see Figure 14: "Gate charge test circuit")	-	24	-	nC
Q _{gs}	Gate-source charge		-	9	-	nC
Q _{gd}	Gate-drain charge		-	8	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = -15 V, I _D = -20 A, R _G = 4.7 Ω, V _{GS} = -10 V (see Figure 13: "Switching times test circuit for resistive load")	-	13.2	-	ns
t _r	Rise time		-	93	-	ns
t _{d(off)}	Turn-off delay time		-	50	-	ns
t _f	Fall time		-	18	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = -40\text{ A}$, $V_{GS} = 0$	-		-1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = -40\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = -24\text{ V}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	20		ns
Q_{rr}	Reverse recovery charge		-	16		nC
I_{RRM}	Reverse recovery current		-	-1.6		A

Notes:

⁽¹⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)



Note: For the P-channel Power MOSFET, current and voltage polarities are reversed.

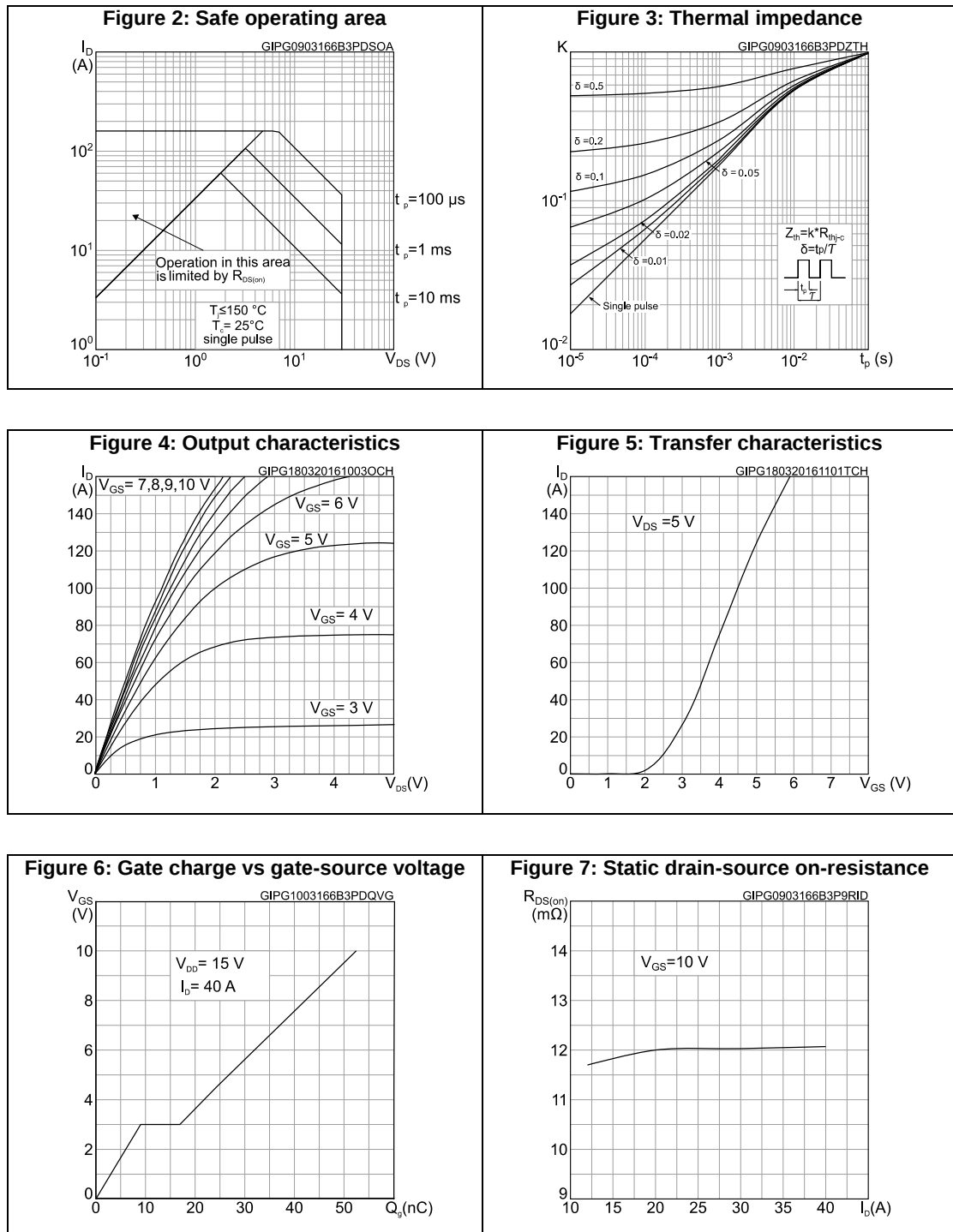


Figure 8: Capacitance variations

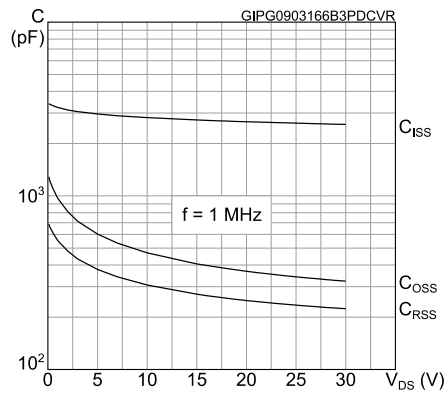


Figure 9: Normalized gate threshold voltage vs temperature

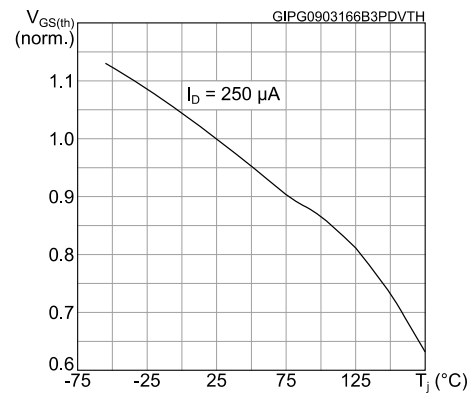


Figure 10: Normalized on-resistance vs temperature

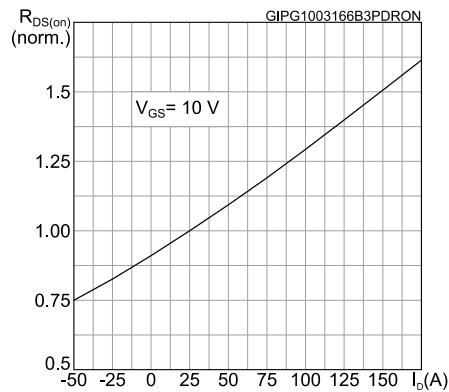


Figure 11: Normalized V(BR)DSS vs temperature

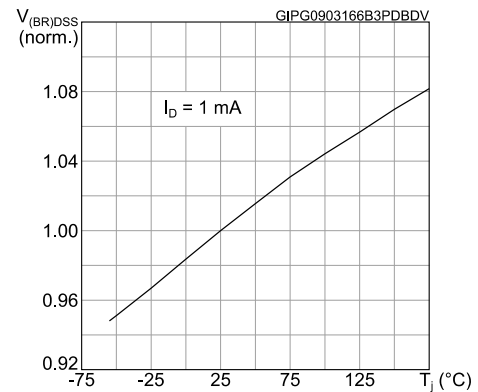
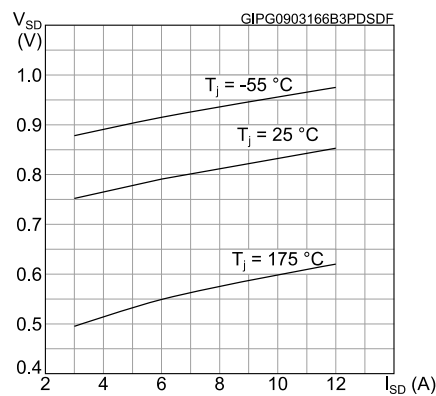


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Switching times test circuit for resistive load

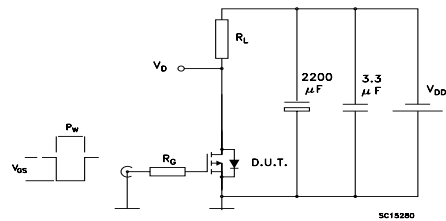


Figure 14: Gate charge test circuit

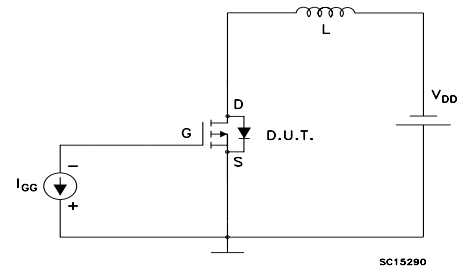
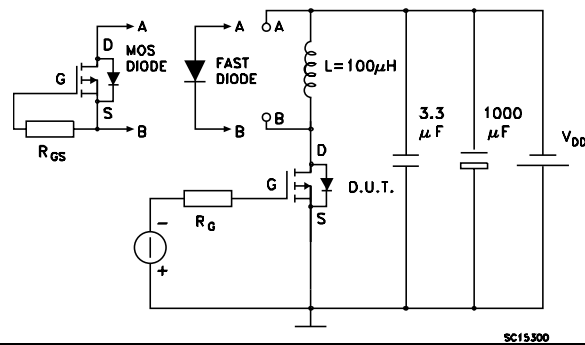


Figure 15: Test circuit for inductive load switching and diode recovery times



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 DPAK (TO252) type A2 mechanical data

Figure 16: DPAK (TO-252) type A2 package outline

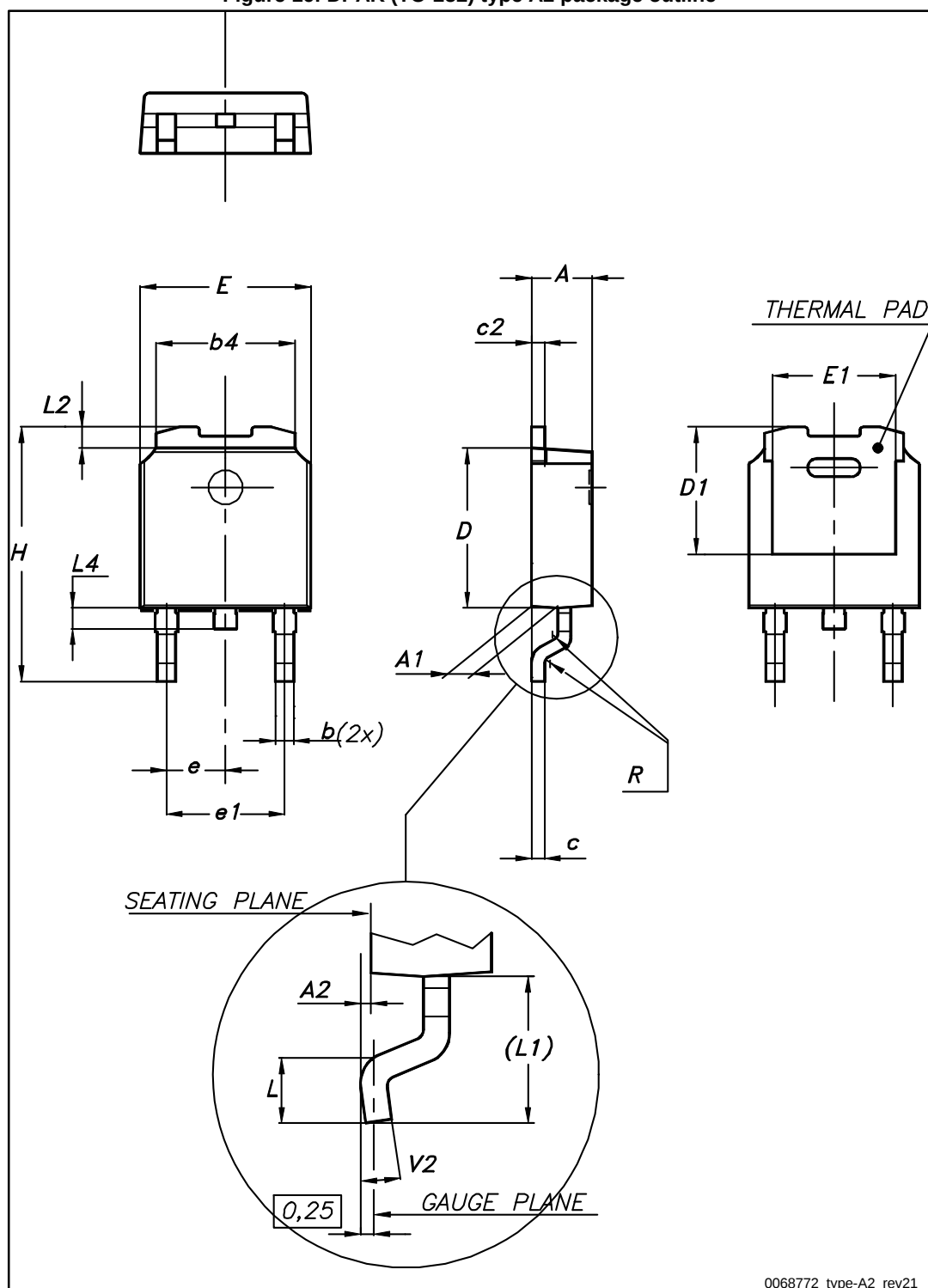
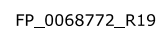


Table 8: DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 17: DPAK (TO-252) recommended footprint (dimensions are in mm)



4.2 DPAK (TO252) packing information

Figure 18: DPAK (TO-252) tape outline

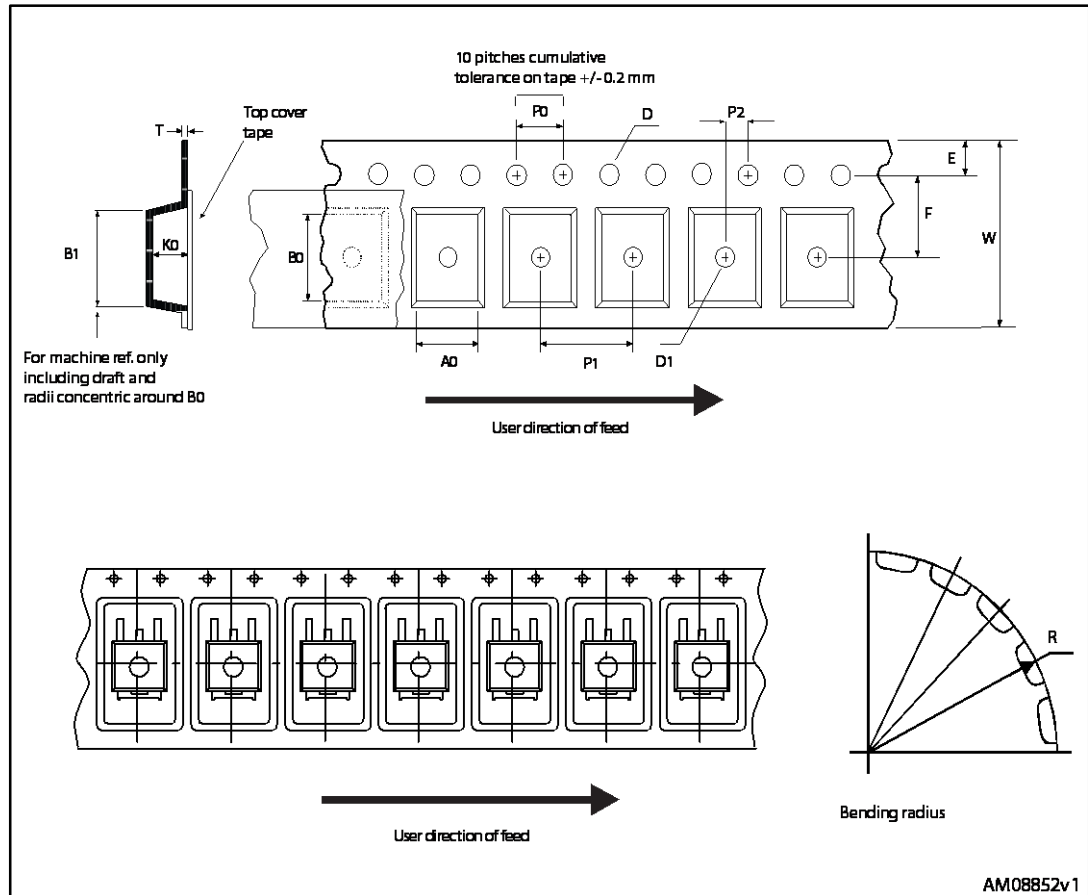


Figure 19: DPAK (TO-252) reel outline

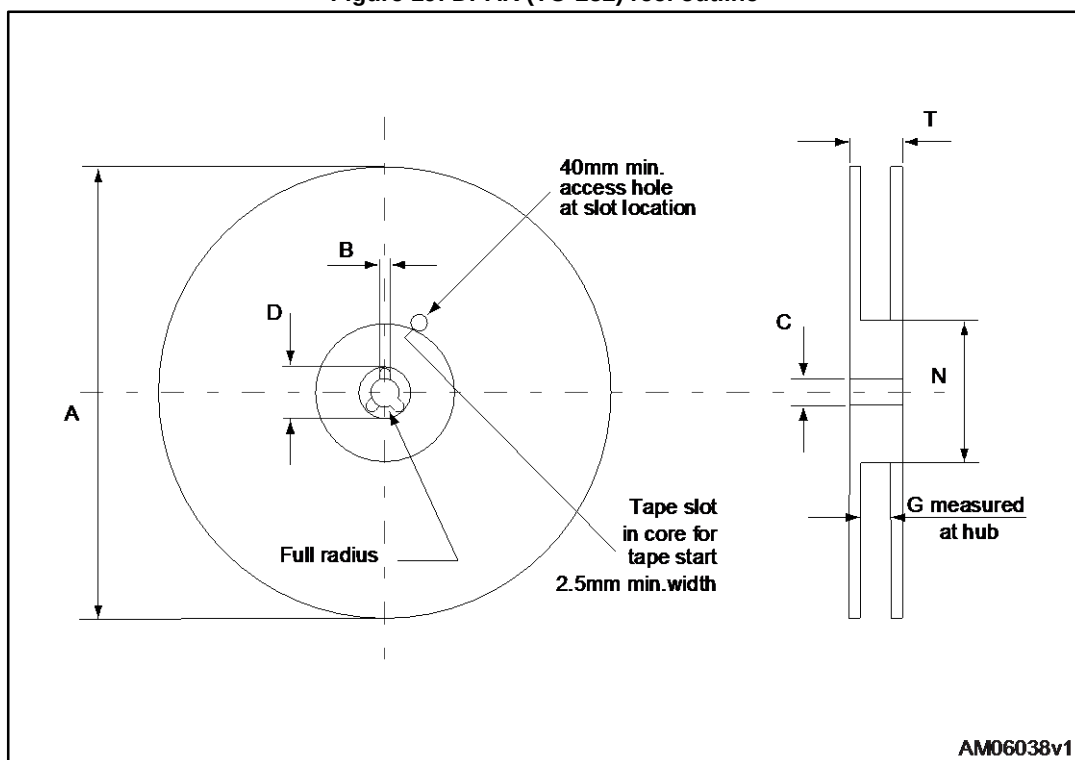


Table 9: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
23-Jan-2014	1	First release.
07-Mar-2016	2	Modified: title and $R_{DS(on)}$ max value. Modified: Table 4: "On /off states", Table 5: "Dynamic", Table 6: "Switching times" and Table 7: "Source drain diode". Minor text changes.
21-Mar-2016	3	Modified: Figure 4: "Output characteristics" and Figure 5: "Transfer characteristics". Minor text changes.
30-Mar-2016	4	Updated title. Minor text changes.

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